

Silicon PNP Power Transistors

2N5954 2N5955 2N5956

DESCRIPTION

- With TO-66 package
- Low collector-emitter saturation voltage
- Excellent safe operating area
- Complement to type 2N6372 2N6373 2N6374

APPLICATIONS

- Designed for driver circuits, switching and amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

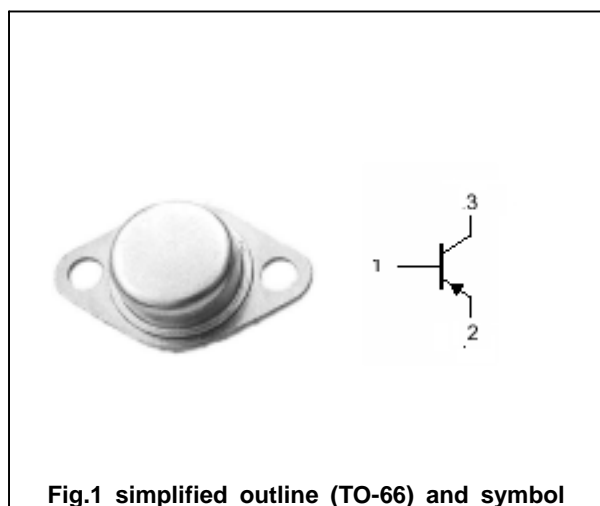


Fig.1 simplified outline (TO-66) and symbol

Absolute maximum ratings($T_a =$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2N5954	90	V
		2N5955	70	
		2N5956	50	
V_{CEO}	Collector-emitter voltage	2N5954	80	V
		2N5955	60	
		2N5956	40	
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		6	A
I_B	Base current		2	A
P_D	Total Power Dissipation	$T_C=25$	40	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-65~200	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R_{th-j-c}	Thermal resistance junction to case	4.3	/W

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(sus)}	Collector-emitter sustaining voltage	2N5954	80			V
		2N5955	60			
		2N5956	40			
V _{CEsat}	Collector-emitter saturation voltage	2N5954			1.0	V
		2N5955				
		2N5956				
V _{BE-1}	Base-emitter on voltage	2N5954			2.0	V
		2N5955				
		2N5956				
V _{BE-2}	Base-emitter on voltage	I _C =6A ; V _{CE} =4V			3.0	V
I _{CEO}	Collector cut-off current	2N5954			1.0	mA
		2N5955				
		2N5956				
I _{CEV}	Collector cut-off current(R _{BE} =100)	V _{CE} =Rated V _{CE} ; V _{BE(off)} =1.5V T _C =150			0.1 2.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			0.1	mA
h _{FE-1}	DC current gain	2N5954		20	100	
		2N5955				
		2N5956				
h _{FE-2}	DC current gain	I _C =6A ; V _{CE} =4V	5			
f _T	Transition frequency	I _C =1A;V _{CE} =4V;f=1.0MHz	5			MHz

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PACKAGE OUTLINE

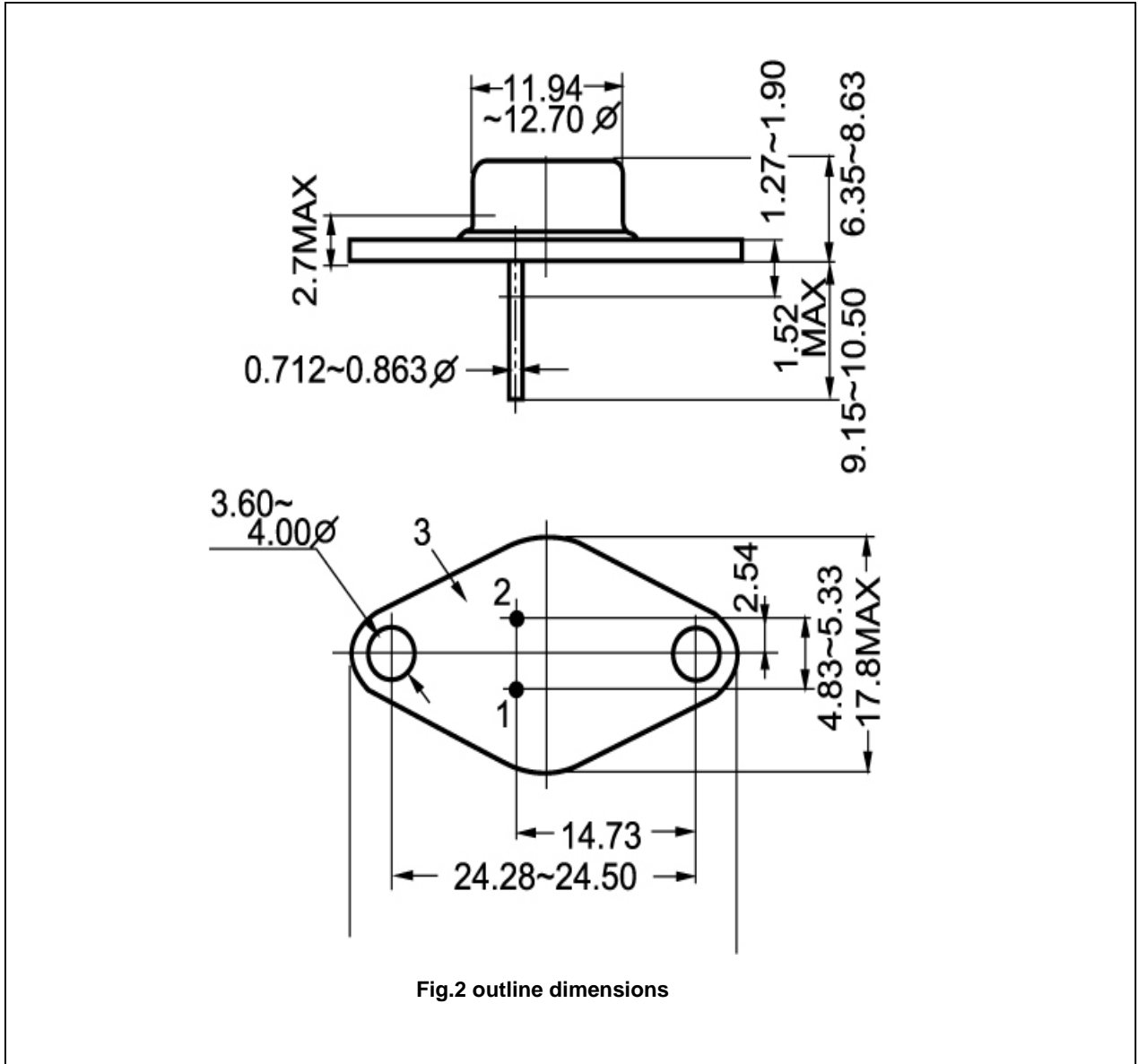


Fig.2 outline dimensions